

ABSTRACT OF THE DISCLOSURE

There are provided a semiconductor device and method for fabricating the device capable of achieving reliable electrical connection by securely directly bonding
5 conductors to each other even though bonding surfaces are polished by a CMP method and solid-state-bonded to each other. By polishing according to the CMP method, a through hole conductor 5 and a grounding wiring layer 10, which are made of copper, become concave in a dish-like shape and
10 lowered in level, causing a dishing portion 17 since they have a hardness lower than that of a through hole insulator 11 made of silicon nitride. The through hole insulator 11 is selectively etched by a reactive ion etching method until the through hole insulator 11 comes to have a height equal
15 to the height of a bottom portion 19 of the dishing portion 17 of the through hole conductor 5. The through hole conductors 5 and 25 are aligned with each other, and the bonding surfaces 12 and 22 are bonded to each other in a solid state bonding manner.

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